Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A semiconductor laser with a semiconductor body, including a laser resonator, comprising:

a plurality of discontinuities formed in a first region of said semiconductor body and arranged in an arrangement such that radiation generated by the semiconductor laser cannot propagate ~~therethrough~~ through said first region, and

a second region of said semiconductor body constituting the laser resonator, said second region being formed by an interruption of said arrangment and having none of said discontinuities formed therein, to enable propagation ~~therethrough~~ of radiation generated by the semiconductor laser through said second region.

2. (currently amended) The semiconductor laser as claimed in claim 1, wherein the resonator ~~(3)~~ has an angled or curved resonator axis.

3. (currently amended) The semiconductor laser as claimed in claim 1, wherein the discontinuities are filled with a filling material, ~~the~~ a refractive index of ~~which differs~~ said filling material being different from ~~the~~ a refractive index of ~~the~~ said semiconductor body ~~(1)~~.

4. (currently amended) The semiconductor laser as claimed in claim 1, wherein ~~the~~ said first and second semiconductor body regions adjoin a filling material, ~~the~~ a refractive index of ~~which differs~~ said filling material being different from ~~the~~ a refractive index of ~~the~~ said first and second semiconductor body regions.

5. (currently amended) An optically pumped semiconductor device with a vertical emitter ~~(13)~~ comprising a quantum well structure ~~(7)~~, wherein ~~the~~ said quantum well structure ~~(7)~~ of ~~the~~ said vertical emitter ~~(13)~~ is optically pumped by at least one semiconductor laser as claimed in claim 1.

6. (currently amended) An optically pumped semiconductor device with a vertical emitter ~~(13)~~ comprising a quantum well structure ~~(7)~~ wherein ~~the~~ said quantum well structure ~~(7)~~ of ~~the~~ said vertical emitter ~~(13)~~ is pumped by a plurality of semiconductor lasers ~~(16a to 16m)~~ as claimed in claim 1, at least one of said semiconductor lasers having a resonator with an angled or curved resonator axis.

7. (currently amended) An optically pumped semiconductor device with a vertical emitter ~~(13)~~ comprising a quantum well structure ~~(7)~~, and with a pump radiation source ~~(20)~~, which generates pump radiation ~~(21)~~ for optically pumping ~~the~~ said quantum well structure ~~(7)~~, comprising:

a waveguide for coupling ~~the~~ said pump radiation ~~(21)~~ into ~~the~~ said quantum well structure ~~(7)~~, wherein said waveguide is laterally delimited at least partly by an arrangement of a

plurality of discontinuities arranged in such a way that ~~the~~ said pump radiation is not capable of propagating within said arrangement.

8. (currently amended) The optically pumped semiconductor device as claimed in claim 7, wherein ~~the~~ said discontinuities are filled with a filling material, ~~the~~ a refractive index of said filling material being different ~~which differs~~ from ~~the~~ a refractive index of ~~the~~ said semiconductor body.

9. (currently amended) The optically pumped semiconductor device as claimed in claim 7, wherein ~~the~~ said semiconductor regions adjoin a filling material, a ~~the~~ refractive index of said filling material being different ~~which differs~~ from ~~the~~ a refractive index of ~~the~~ said semiconductor regions.

10. (currently amended) The optically pumped semiconductor device as claimed in claim 7, wherein ~~the~~ said pump radiation source is a semiconductor laser with a semiconductor body, including a laser resonator, comprising:

a plurality of discontinuities formed in a first region of said semiconductor body and arranged such that radiation generated by ~~the~~ said semiconductor laser cannot propagate ~~therethrough~~ through said first region, and

a second region of said semiconductor body constituting ~~the~~ said laser resonator, said second region having none of said discontinuities formed therein, to enable propagation ~~therethrough~~ of radiation generated by the semiconductor laser through said second region.

11. (currently amended) The optically pumped semiconductor device as claimed in claim 5, wherein ~~the~~ said vertical emitter ~~(13)~~ and ~~the~~ said semiconductor laser are grown epitaxially on a common substrate ~~(8)~~.

12. (currently amended) The optically pumped semiconductor device as claimed in claim 7, wherein ~~the~~ said vertical emitter and said pump radiation source are ~~(20) is~~ grown epitaxially on a common substrate ~~(8)~~.

13. (original) The optically pumped semiconductor device as claimed in claim 7, wherein said discontinuities comprise a periodic arrangement of cutouts.

14. (original) The optically pumped semiconductor device as claimed in claim 7, wherein said discontinuities comprise a periodic arrangement of semiconductor regions.

15. (original) The semiconductor laser as claimed in claim 1, wherein said discontinuities comprise a periodic arrangement of cutouts.

16. (original) The semiconductor laser as claimed in claim 1, wherein said discontinuities comprise a periodic arrangement of semiconductor regions.

17. (new) The semiconductor as claimed in claim 1, wherein said semiconductor body comprises outer side areas forming resonator mirrors of said laser resonator.

18. (new) The optically pumped semiconductor device as claimed in claim 7, wherein said waveguide and said quantum well structure are monolithically integrated.

19 (new) The optically pumped semiconductor device as claimed in claim 10, wherein said discontinuities are arranged in an arrangement, said second region being formed by an interruption of said arrangement.